



Abstract

The invention relates to a microelectronics and more particularly to a bipolar static induction transistor.

The invention allows to create the transistor which can operate on supply pressure 220 volt and over, that is the transistor can be both close and open, with any polarity of a voltage on drain-source. It simplifies designing of many circuits and makes it possible to create circuits which cannot be produced with any other types of transistors. Besides, the transistor has high technical characteristics: high current density and high switching power. It makes it possible to apply the transistor for production, transfer and use of electric energy.

This is achieved by disposing elements of the bipolar static induction transistor - a gate, a source and a channel - on each of sides of a substrate.

The invention is explained with three drawings.